Silicon Epitaxial Planar Zener Diodes

in MiniMELF case especially for automatic insertion. The Zener voltages are graded according to the international E24 standard. Smaller voltage tolerances and higher Zener voltages are upon request.

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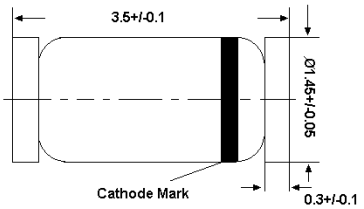


Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	500 [1)]	mW
Junction Temperature	T_j	175	°C
Storage Temperature Range	T_{stg}	- 55 to + 175	°C
[1)] Valid provided that electrodes are kept at ambient temperature			

Characteristics at T_a = 25 °C

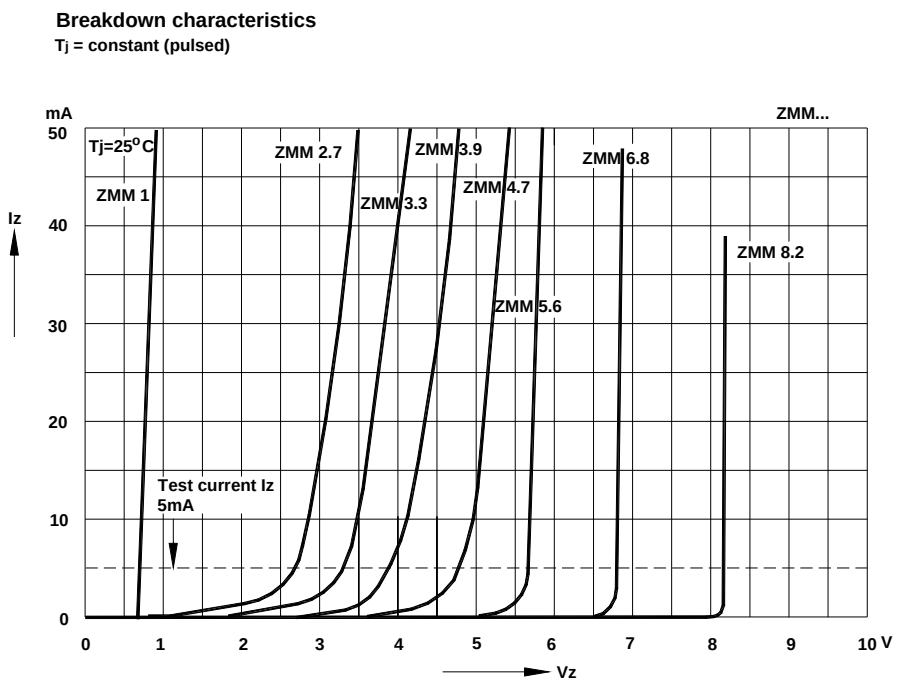
Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air	R_{thA}	0.3 [1)]	K/mW
Forward Voltage at I_F = 100 mA	V_F	1	V
[1)] Valid provided that electrodes are kept at ambient temperature			

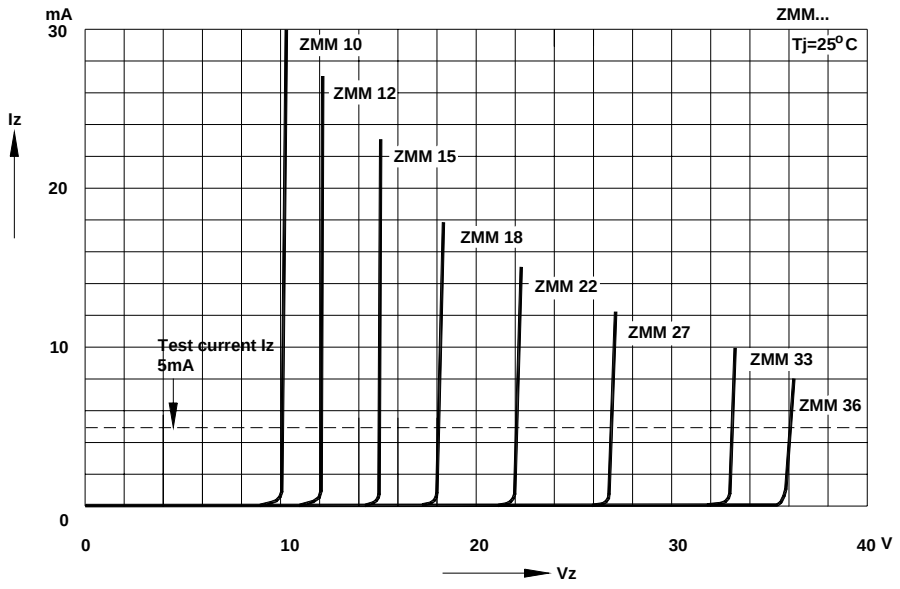
Characteristics at T_a = 25 °C

Type	Zener Voltage Range [1]			Dynamic Resistance			Reverse Leakage Current			Temp. Coefficient of Zener Voltage
	V_{Znom}	V_{ZT}	at I_{ZT}	Z_{ZT}	Z_{ZK}	at I_{ZK}	T_a = 25 °C	T_a = 125 °C	at V_R	
	(V)	(V)	(mA)	Max. (Ω)	Max. (Ω)	(mA)	Max. (μA)	Max. (μA)	(V)	TKvz (%/K)
ZMM1V0	0.75	0.7...0.8	5	8	50	1	-	-	-	-0.26...-0.23
ZMM2V0	2	1.8...2.15	5	85	600	1	100	200	1	-0.09...-0.06
ZMM2V2	2.2	2.08...2.33	5	85	600	1	75	160	1	-0.09...-0.06
ZMM2V4	2.4	2.28...2.56	5	85	600	1	50	100	1	-0.09...-0.06
ZMM2V7	2.7	2.5...2.9	5	85	600	1	10	50	1	-0.09...-0.06
ZMM3V0	3	2.8...3.2	5	85	600	1	4	40	1	-0.08...-0.05
ZMM3V3	3.3	3.1...3.5	5	85	600	1	2	40	1	-0.08...-0.05
ZMM3V6	3.6	3.4...3.8	5	85	600	1	2	40	1	-0.08...-0.05
ZMM3V9	3.9	3.7...4.1	5	85	600	1	2	40	1	-0.08...-0.05
ZMM4V3	4.3	4...4.6	5	75	600	1	1	20	1	-0.06...-0.03
ZMM4V7	4.7	4.4...5	5	60	600	1	0.5	10	1	-0.05...+0.02
ZMM5V1	5.1	4.8...5.4	5	35	550	1	0.1	2	1	-0.02...+0.02
ZMM5V6	5.6	5.2...6	5	25	450	1	0.1	2	1	-0.05...+0.05
ZMM6V2	6.2	5.8...6.6	5	10	200	1	0.1	2	2	0.03...0.06
ZMM6V8	6.8	6.4...7.2	5	8	150	1	0.1	2	3	0.03...0.07
ZMM7V5	7.5	7...7.9	5	7	50	1	0.1	2	5	0.03...0.07
ZMM8V2	8.2	7.7...8.7	5	7	50	1	0.1	2	6.2	0.03...0.08
ZMM9V1	9.1	8.5...9.6	5	10	50	1	0.1	2	6.8	0.03...0.09
ZMM10	10	9.4...10.6	5	15	70	1	0.1	2	7.5	0.03...0.1
ZMM11	11	10.4...11.6	5	20	70	1	0.1	2	8.2	0.03...0.11
ZMM12	12	11.4...12.7	5	20	90	1	0.1	2	9.1	0.03...0.11
ZMM13	13	12.4...14.1	5	26	110	1	0.1	2	10	0.03...0.11
ZMM15	15	13.8...15.6	5	30	110	1	0.1	2	11	0.03...0.11
ZMM16	16	15.3...17.1	5	40	170	1	0.1	2	12	0.03...0.11
ZMM18	18	16.8...19.1	5	50	170	1	0.1	2	13	0.03...0.11
ZMM20	20	18.8...21.2	5	55	220	1	0.1	2	15	0.03...0.11
ZMM22	22	20.8...23.3	5	55	220	1	0.1	2	16	0.04...0.12
ZMM24	24	22.8...25.6	5	80	220	1	0.1	2	18	0.04...0.12
ZMM27	27	25.1...28.9	5	80	220	1	0.1	2	20	0.04...0.12
ZMM30	30	28...32	5	80	220	1	0.1	2	22	0.04...0.12
ZMM33	33	31...35	5	80	220	1	0.1	2	24	0.04...0.12
ZMM36	36	34...38	5	80	220	1	0.1	2	27	0.04...0.12
ZMM39	39	37...41	2.5	90	500	0.5	0.1	5	30	0.04...0.12
ZMM43	43	40...46	2.5	90	500	0.5	0.1	5	33	0.04...0.12
ZMM47	47	44...50	2.5	110	600	0.5	0.1	5	36	0.04...0.12
ZMM51	51	48...54	2.5	125	700	0.5	0.1	10	39	0.04...0.12
ZMM56	56	52...60	2.5	135	700	0.5	0.1	10	43	0.04...0.12
ZMM62	62	58...66	2.5	150	1000	0.5	0.1	10	47	0.04...0.12
ZMM68	68	64...72	2.5	200	1000	0.5	0.1	10	51	0.04...0.12
ZMM75	75	70...79	2.5	250	1000	0.5	0.1	10	56	0.04...0.12

[1] Tested with pulses t_p = 20 ms.

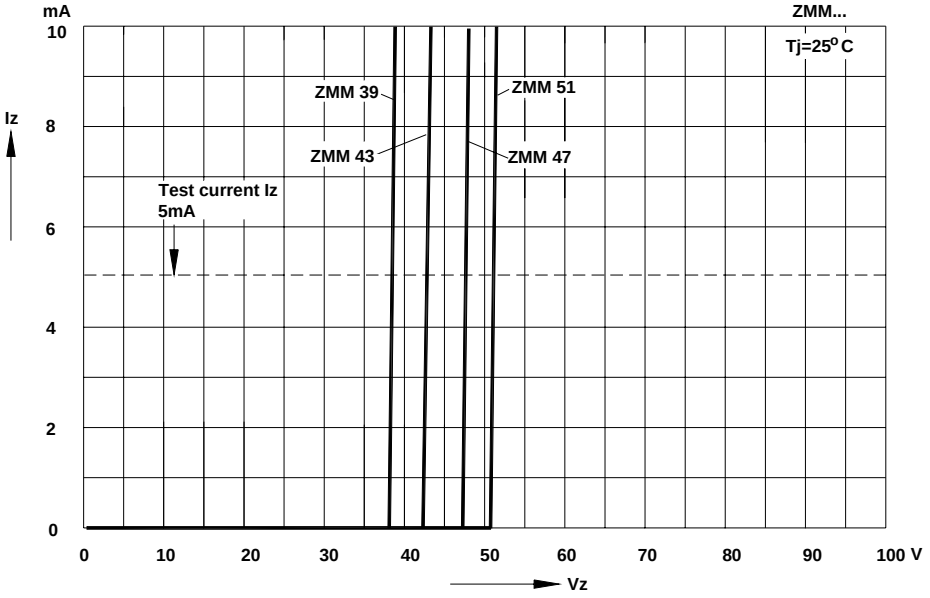
[2] The ZMM1 is a silicon diode with operation in forward direction. Hence, the index of all parameters should be "F" instead of "Z". Connect the cathode electrode to the negative pole.


Breakdown characteristics
Tj = constant (pulsed)
mA
ZMM...
Tj=25°C
ZMM 1
ZMM 2.7
ZMM 3.3
ZMM 3.9
ZMM 4.7
ZMM 5.6
ZMM 6.8
ZMM 8.2
Iz
Test current Iz
5mA
0
10
20
30
40
50
0
1
2
3
4
5
6
7
8
9
10 V
Vz

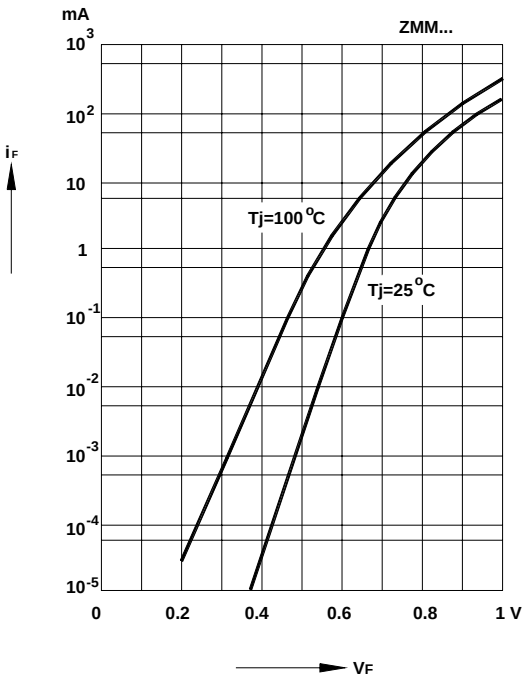

Breakdown characteristics
Tj = constant (pulsed)
mA
ZMM...
Tj=25°C
ZMM 10
ZMM 12
ZMM 15
ZMM 18
ZMM 22
ZMM 27
ZMM 33
ZMM 36
Iz
Test current Iz
5mA
0
10
20
30
0
10
20
30
40 V
Vz

Breakdown characteristics

T_j = constant (pulsed)

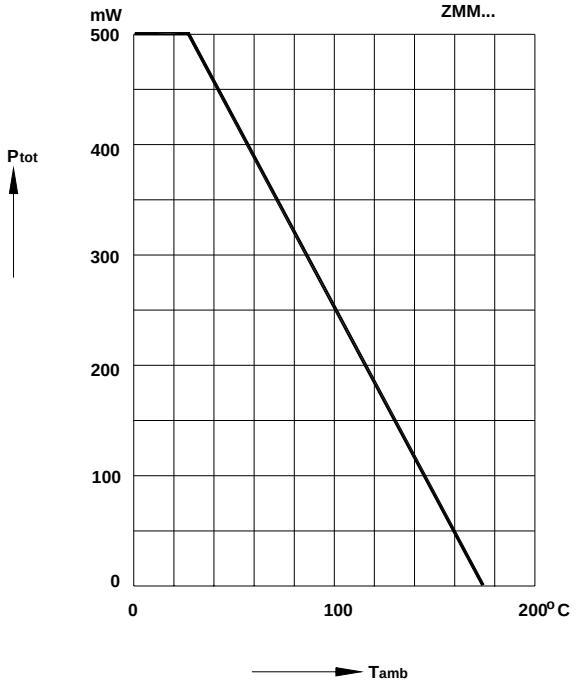


Forward characteristics



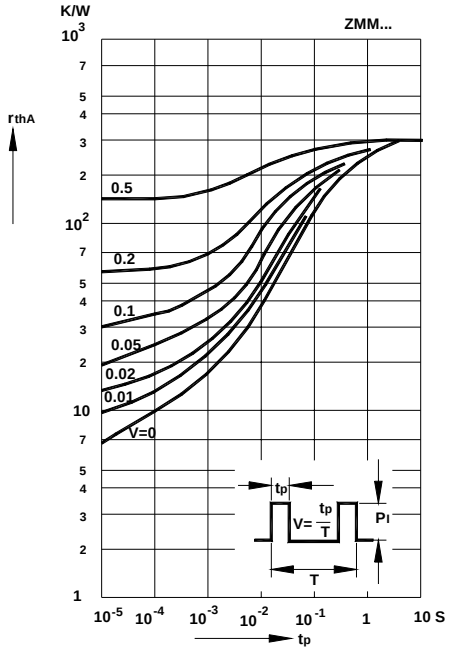
Admissible power dissipation versus ambient temperature

Valid provided that electrodes are kept at ambient temperature.

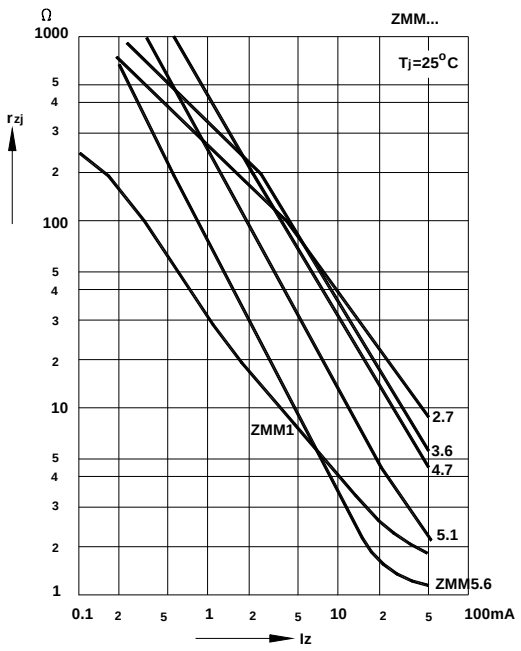


Pulse thermal resistance versus pulse duration

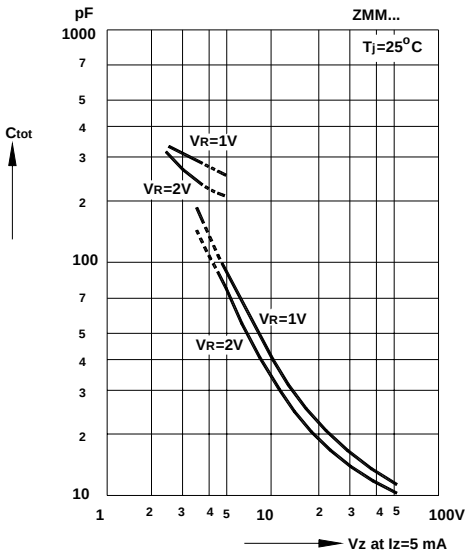
Valid provided that the electrodes are kept at ambient temperature.



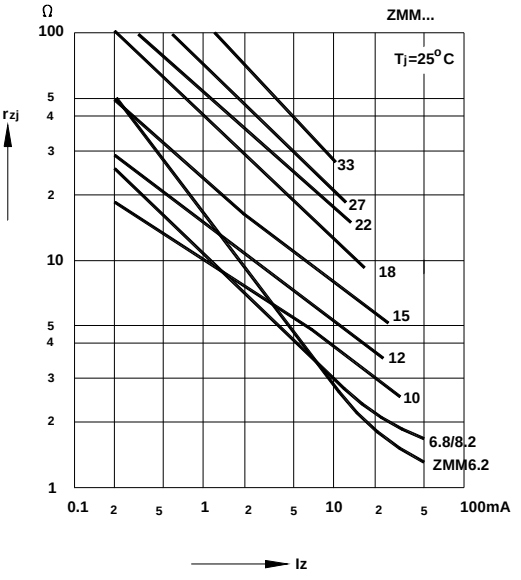
Dynamic resistance versus Zener current

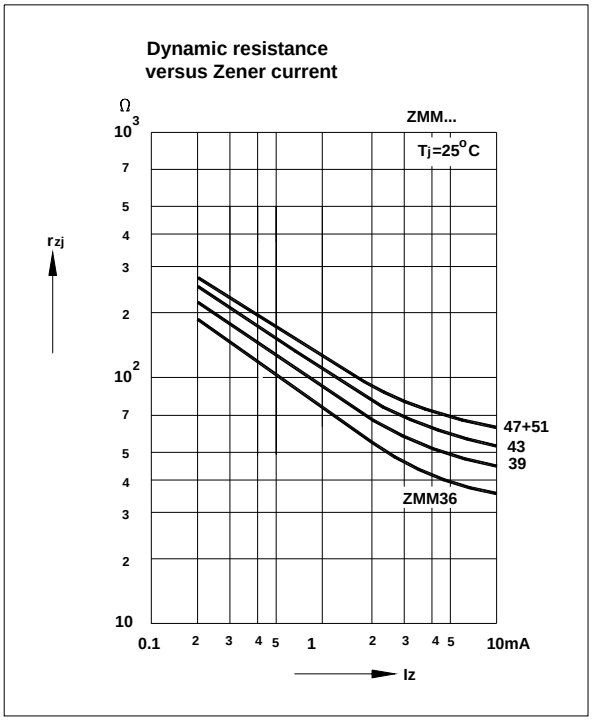


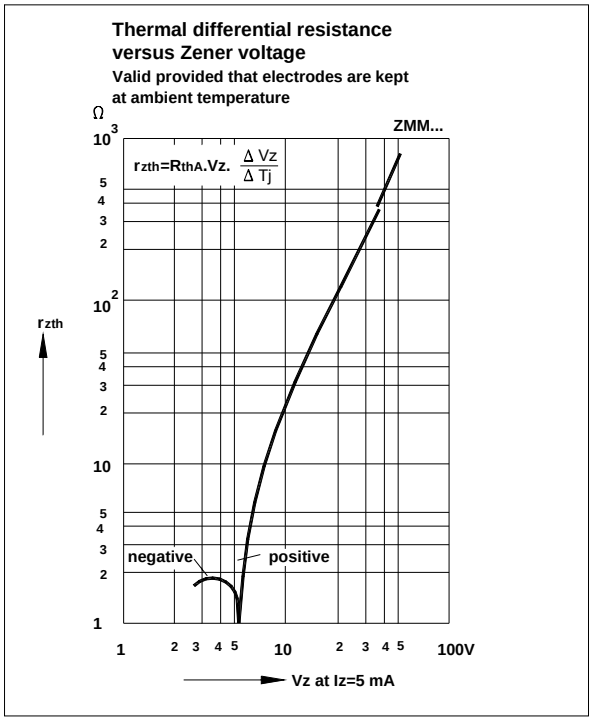
Capacitance versus Zener voltage

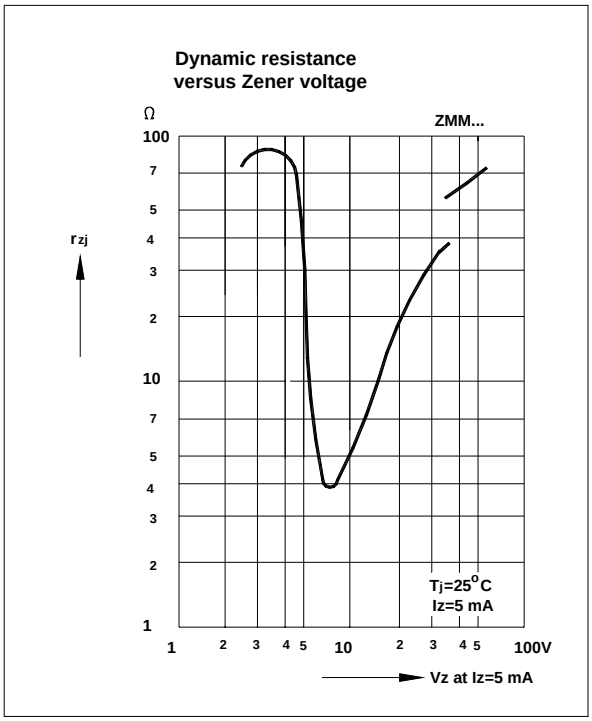


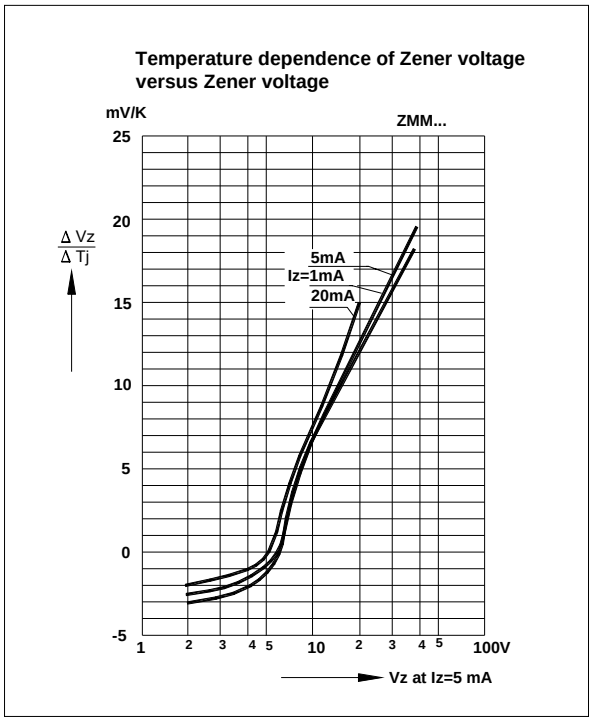
Dynamic resistance versus Zener current



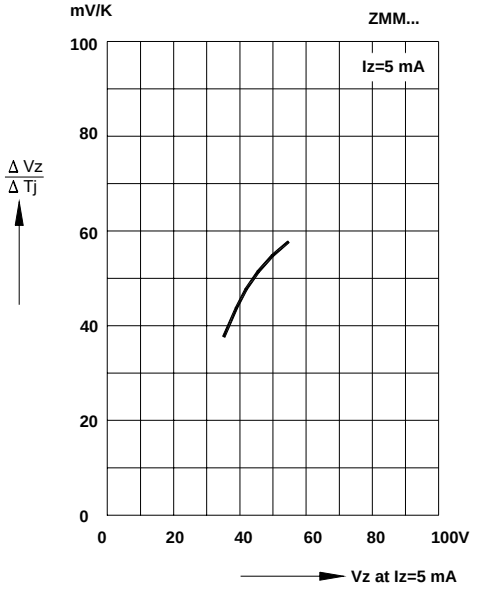

Dynamic resistance
versus Zener current
Ω
ZMM...
Tj=25°C
rzj
47+51
43
39
ZMM36
0.1
1
10mA
Iz


Thermal differential resistance
versus Zener voltage
Valid provided that electrodes are kept
at ambient temperature
Ω
ZMM...
rzth=RthA.Vz. Δ Vz / Δ Tj
rzth
negative
positive
1
10
100V
Vz at Iz=5 mA

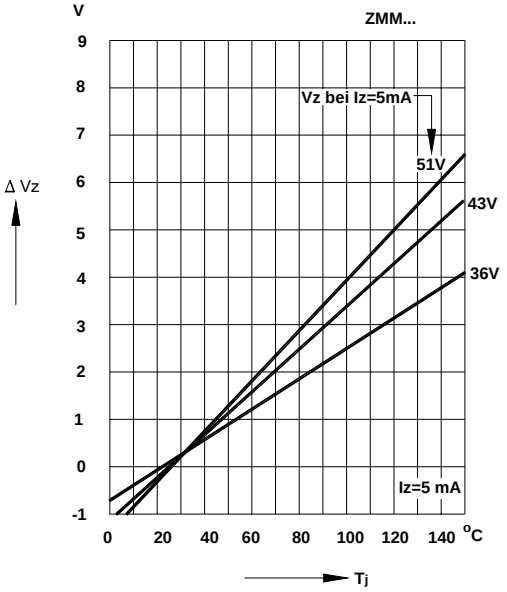

Dynamic resistance
versus Zener voltage
Ω
ZMM...
rzj
Tj=25°C
Iz=5 mA
1
10
100V
Vz at Iz=5 mA


Temperature dependence of Zener voltage
versus Zener voltage
mV/K
ZMM...
Δ Vz / Δ Tj
5mA
Iz=1mA
20mA
1
10
100V
Vz at Iz=5 mA

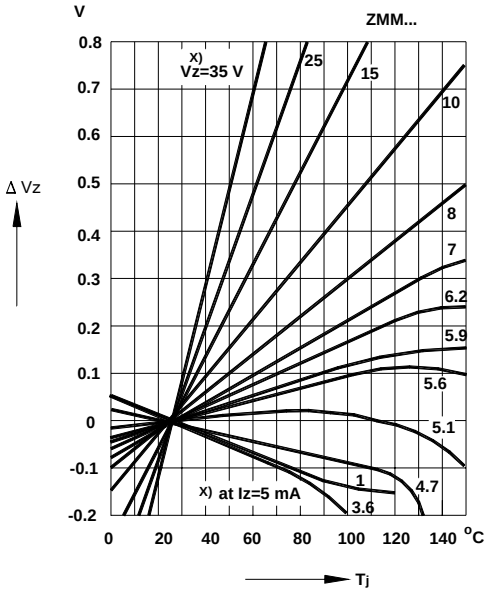
Temperature dependence of Zener voltage versus Zener voltage



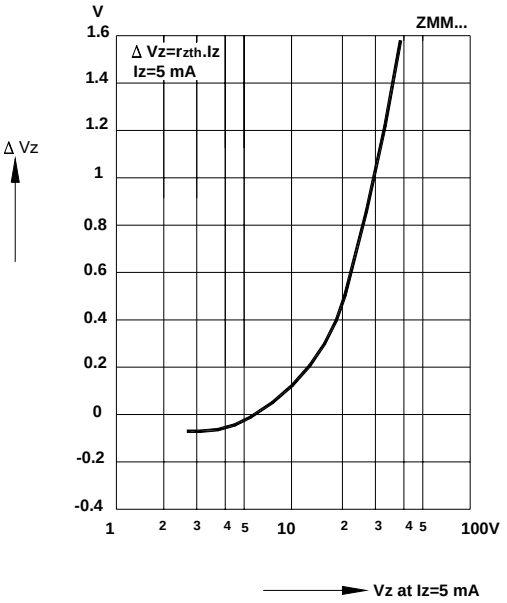
Change of Zener voltage versus junction temperature

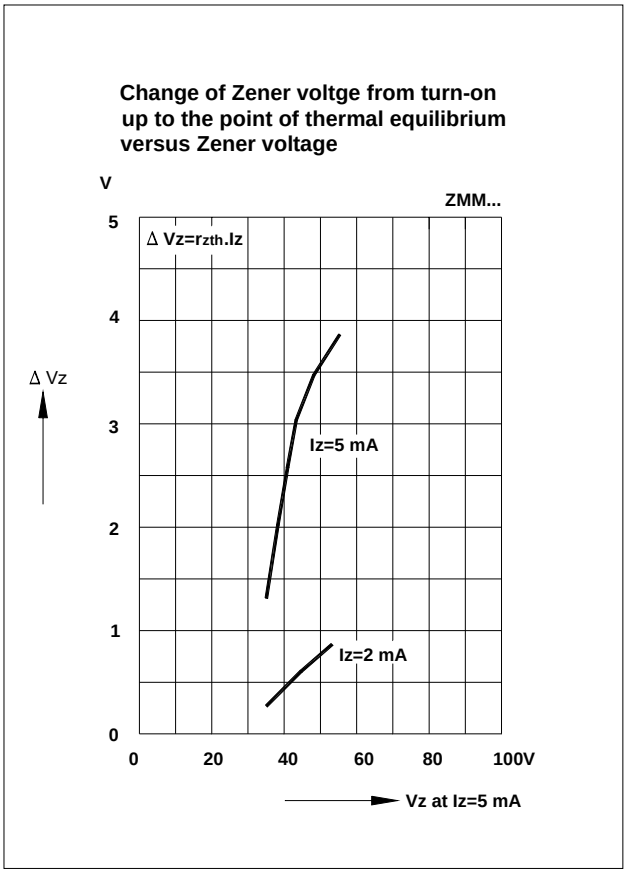


Change of Zener voltage versus junction temperature



Change of Zener voltge from turn-on up to the point of thermal equilibrium versus Zener voltage




Change of Zener voltge from turn-on
up to the point of thermal equilibrium
versus Zener voltage
V
ZMM...
Δ Vz=rzth.Iz
Δ Vz
5
4
3
2
1
0
Iz=5 mA
Iz=2 mA
0
20
40
60
80
100V
Vz at Iz=5 mA